

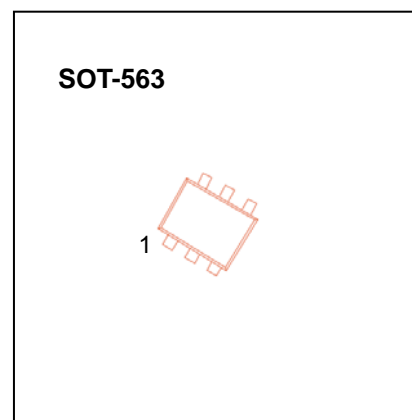
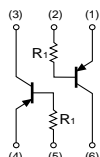
General purpose transistors (dual digital transistors)

FEATURES

- Two DTA114T chips in a package

Marking: B4

Equivalent circuit



Absolute maximum ratings ($T_a=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-100	mA
P_C	Collector Power Dissipation	150	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}$, $I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}$, $I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}$, $I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}$, $I_C=0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE}=-5\text{V}$, $I_C=-1\text{mA}$	100		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}$, $I_B=-1\text{mA}$			-0.3	V
Transition frequency	f_T	$V_{CE}=-10\text{V}$, $I_C=-5\text{mA}$, $f=100\text{MHz}$		250		MHz
Input resistance	R_1	-	7		13	Ω